Power Transistors

Panasonic

2SB0937 (2SB937), 2SB0937A (2SB937A)

Silicon PNP epitaxial planar type Darlington

For power amplification and switching Complementary to 2SD1260, 2SD1260A

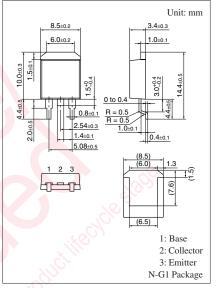
Features

- High forward current transfer ratio h_{FE}
- High-speed switching
- N type package enabling direct soldering of the radiating fin to the printed circuit board, etc. of small electronic equipment.

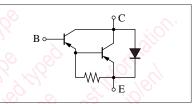
Absolute Maximum Ratings $T_C = 25^{\circ}C$

Parameter		Symbol	Rating	Unit
Collector-base voltage	2SB0937	V _{CBO}	-60	V
(Emitter open)	2SB0937A		-80	
Collector-emitter voltage	2SB0937	V _{CEO}	-60	V
(Base open)	2SB0937A		-80	
Emitter-base voltage (Collector open)		V _{EBO}	-5	v
Collector current	I _C	-2	Α	
Peak collector current	I _{CP}	-4	А	
Collector power dissipation		P _C	35	W
	$T_a = 25^{\circ}C$		1.3	
Junction temperature		Tj	150	°C
Storage temperature		T _{stg}	-55 to +150	S°C
			20.	

Electrical Characteristics $T_C = 25^{\circ}C \pm 3^{\circ}C$



Note) Self-supported type package is also prepared. Internal Connection



Unit

v

V

mА

mA

Conditions Parameter Symbol Min Typ Max 2SB0937 VCEO $I_{\rm C} = -30 \text{ mA}, I_{\rm B} = 0$ -60 Collector-emitter voltage (Base open) 2SB0937A -80Base-emitter voltage $V_{CE} = -4 V_{IC} = -2 A$ VBE -2.8 $V_{CB} = -60 \text{ V}, I_E = 0$ Collector-base cutoff 2SB0937 I_{CBO} -1 current (Emitter open) $V_{CB} = -80 \text{ V}, I_E = 0$ 2SB0937A $^{-1}$ 2SB0937 $V_{CE} = -30 \text{ V}, I_B = 0$ -2I_{CEO} Collector-emitter cutoff current (Base open) 2SB0937A $V_{CE} = -40 \text{ V}, I_{B} = 0$ -2 E

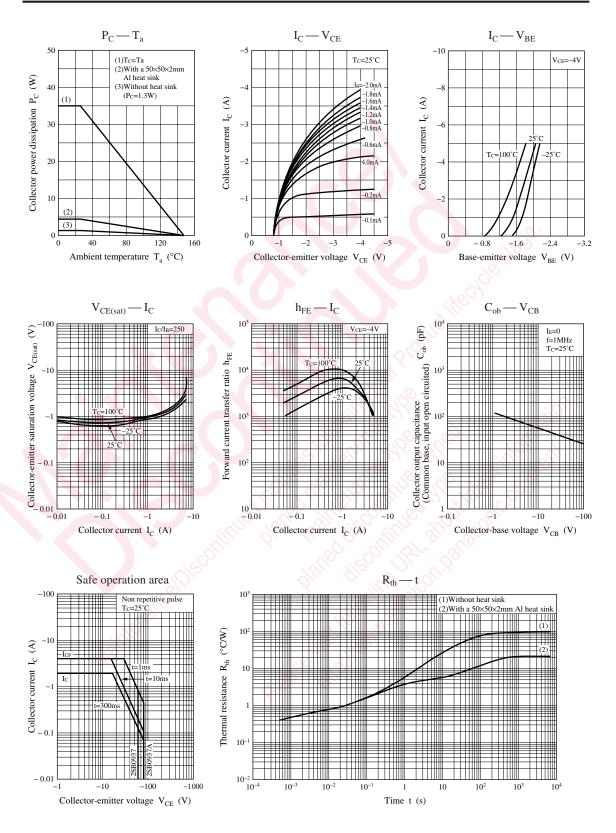
Emitter-base cutoff current (Collector open)	I _{EBO}	$V_{\rm EB} = -5 \ V, I_{\rm C} = 0$			-2	mA			
Forward current transfer ratio	h _{FE1}	$V_{CE} = -4 V, I_C = -1 A$	1 0 0 0						
	h _{FE2} *	$V_{CE} = -4 V, I_C = -2 A$	2000		10 000				
Collector-emitter saturation voltage	V _{CE(sat)}	$I_{\rm C} = -2$ A, $I_{\rm B} = -8$ mA			-2.5	V			
Transition frequency	f_{T}	$V_{CE} = -10 \text{ V}, I_C = -0.5 \text{ A}, f = 1 \text{ MHz}$		20		MHz			
Turn-on time	ton	$I_{\rm C} = -2 {\rm A},$		0.4		μs			
Strage time	t _{stg}	$I_{B1} = -8 \text{ mA}, I_{B2} = 8 \text{ mA}$		1.5		μs			
Fall time	t _f	$V_{\rm CC} = -50 \text{ V}$		0.5		μs			
Note) 1 Measuring methods are based on IAPANESE INDUSTRIAL STANDARD US C 7030 measuring methods for transistory									

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors. 2. *: Rank classification

> Rank Q h_{FE1} 2000 to 5000 4000 to 10000 Note) The part number in the parenthesis shows conventional part number.

Ρ

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